74AUP2G38

Low-power dual 2-input NAND gate; open drain

Rev. 9 — 26 March 2019

Product data sheet

1. General description

The 74AUP2G38 provides the dual 2-input NAND gate with open-drain output. The output of the device is an open drain and can be connected to other open-drain outputs to implement active-LOW wired-OR or active-HIGH wired-AND functions.

Schmitt trigger action at all inputs makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 0.8 V to 3.6 V.

This device ensures a very low static and dynamic power consumption across the entire V_{CC} range from 0.8 V to 3.6 V.

This device is fully specified for partial Power-down applications using I_{OFF} . The I_{OFF} circuitry disables the output, preventing a damaging backflow current through the device when it is powered down.

2. Features and benefits

- Wide supply voltage range from 0.8 V to 3.6 V
- · High noise immunity
- · Complies with JEDEC standards:
 - JESD8-12 (0.8 V to 1.3 V)
 - JESD8-11 (0.9 V to 1.65 V)
 - JESD8-7 (1.2 V to 1.95 V)
 - JESD8-5 (1.8 V to 2.7 V)
 - JESD8-B (2.7 V to 3.6 V)
- ESD protection:
 - HBM JESD22-A114F Class 3A exceeds 5000 V
 - MM JESD22-A115-A exceeds 200 V
 - CDM JESD22-C101E exceeds 1000 V
- Low static power consumption; I_{CC} = 0.9 μA (maximum)
- Latch-up performance exceeds 100 mA per JESD78B Class II
- Inputs accept voltages up to 3.6 V
- Low noise overshoot and undershoot < 10 % of V_{CC}
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from -40 °C to +85 °C and -40 °C to +125 °C



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3. Ordering information

Table 1. Ordering information

Type number	Package							
	Temperature range	Name	Description	Version				
74AUP2G38DC	-40 °C to +125 °C	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1				
74AUP2G38GT	-40 °C to +125 °C	XSON8	plastic extremely thin small outline package; no leads; 8 terminals; body 1 × 1.95 × 0.5 mm	SOT833-1				
74AUP2G38GF	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1 × 0.5 mm	SOT1089				
74AUP2G38GM	-40 °C to +125 °C	XQFN8	plastic, extremely thin quad flat package; no leads; 8 terminals; body 1.6 × 1.6 × 0.5 mm	SOT902-2				
74AUP2G38GN	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.2 × 1.0 × 0.35 mm	SOT1116				
74AUP2G38GS	-40 °C to +125 °C	XSON8	extremely thin small outline package; no leads; 8 terminals; body 1.35 × 1.0 × 0.35 mm	SOT1203				

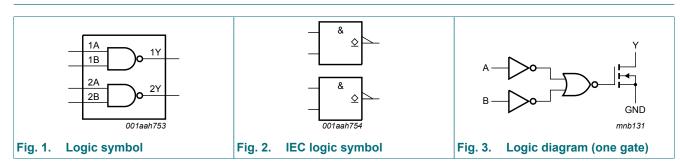
4. Marking

Table 2. Marking codes

Marking code [1]
a38
a38
аВ
a38
аВ
аВ

^[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

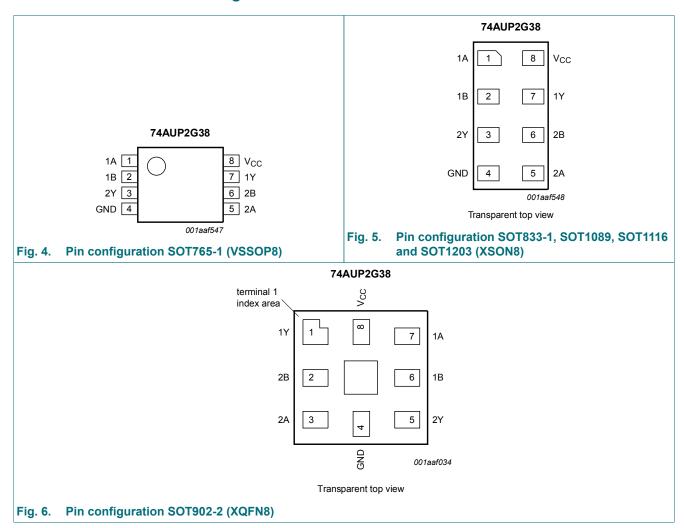
5. Functional diagram



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6. Pinning information

6.1. Pinning



6.2. Pin description

Table 3. Pin description

Symbol	Pin	Pin		
	SOT765-1, SOT833-1, SOT1089, SOT1116 and SOT1203	SOT902-2		
1A, 2A	1, 5	7, 3	data input	
1B, 2B	2, 6	6, 2	data input	
GND	4	4	ground (0 V)	
1Y, 2Y	7, 3	1, 5	data output	
V _{CC}	8	8	supply voltage	

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7. Functional description

Table 4. Function table

H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF state.

Input	Output	
nA	nB	nY
L	L	Z
L	Н	Z
Н	L	Z
Н	Н	L

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
I _{IK}	input clamping current	V _I < 0 V	-50	-	mA
VI	input voltage	[1]	-0.5	+4.6	V
I _{OK}	output clamping current	V _O < 0 V	-50	-	mA
Vo	output voltage	Active mode and Power-down mode [1]	-0.5	+4.6	V
I _O	output current	$V_O = 0 V \text{ to } V_{CC}$	-	+20	mA
I _{CC}	supply current		-	+50	mA
I _{GND}	ground current		-50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _{tot}	total power dissipation	$T_{amb} = -40 ^{\circ}\text{C to } +125 ^{\circ}\text{C}$ [2]	-	250	mW

^[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

9. Recommended operating conditions

Table 6. Operating conditions

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		8.0	3.6	V
VI	input voltage		0	3.6	V
V _O	output voltage	Active mode and Power-down mode	0	3.6	V
T _{amb}	ambient temperature		-40	+125	°C
Δt/ΔV	input transition rise and fall rate	V _{CC} = 0.8 V to 3.6 V	0	200	ns/V

^[2] For VSSOP8 packages: above 110 °C the value of P_{tot} derates linearly at 8.0 mW/K.

For XSON8 and XQFN8 packages: above 118 °C the value of Ptot derates linearly with 7.8 mW/K.

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10. Static characteristics

Table 7. Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
T _{amb} = 2	25 °C				-1	
V _{IH}	HIGH-level input	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
	voltage	V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
	voltage	V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.31	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.31	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.31	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.44	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.31	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.44	V
I _I	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.1	μA
l _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.1	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.2	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.2	μΑ
I _{CC}	supply current	V_{I} = GND or V_{CC} ; I_{O} = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.5	μΑ
Δl _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	40	μΑ
Cı	input capacitance	V_{CC} = 0 V to 3.6 V; V_I = GND or V_{CC}	-	0.7	-	pF
Co	output capacitance	$V_O = GND; V_{CC} = 0 V$	-	0.9	-	pF
T _{amb} = -	40 °C to +85 °C					
V _{IH}	HIGH-level input	V _{CC} = 0.8 V	0.70V _{CC}	-	-	V
	voltage	V _{CC} = 0.9 V to 1.95 V	0.65V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	V _{CC} = 0.8 V	-	-	0.30V _{CC}	V
	voltage	V _{CC} = 0.9 V to 1.95 V	-	-	0.35V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.1	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.3V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.37	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.35	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.33	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.45	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.33	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.45	V
l _l	input leakage current	V _I = GND to 3.6 V; V _{CC} = 0 V to 3.6 V	-	-	±0.5	μΑ
I _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.5	μΑ
l _{OFF}	power-off leakage current	$V_1 \text{ or } V_0 = 0 \text{ V to } 3.6 \text{ V}; V_{CC} = 0 \text{ V}$	-	-	±0.5	μΑ
Δl _{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.6	μΑ
I _{CC}	supply current	V_{I} = GND or V_{CC} ; I_{O} = 0 A; V_{CC} = 0.8 V to 3.6 V	-	-	0.9	μΑ
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	50	μΑ
T _{amb} = -4	40 °C to +125 °C				1	
V _{IH}	HIGH-level input voltage	V _{CC} = 0.8 V	0.75V _{CC}	-	-	V
		V _{CC} = 0.9 V to 1.95 V	0.70V _{CC}	-	-	V
		V _{CC} = 2.3 V to 2.7 V	1.6	-	-	V
		V _{CC} = 3.0 V to 3.6 V	2.0	-	-	V
V _{IL}	LOW-level input	V _{CC} = 0.8 V	-	-	0.25V _{CC}	V
	voltage	V _{CC} = 0.9 V to 1.95 V	-	-	0.30V _{CC}	V
		V _{CC} = 2.3 V to 2.7 V	-	-	0.7	V
		V _{CC} = 3.0 V to 3.6 V	-	-	0.9	V
V _{OL}	LOW-level output	$V_I = V_{IH}$ or V_{IL}				
	voltage	I _O = 20 μA; V _{CC} = 0.8 V to 3.6 V	-	-	0.11	V
		I _O = 1.1 mA; V _{CC} = 1.1 V	-	-	0.33V _{CC}	V
		I _O = 1.7 mA; V _{CC} = 1.4 V	-	-	0.41	V
		I _O = 1.9 mA; V _{CC} = 1.65 V	-	-	0.39	V
		I _O = 2.3 mA; V _{CC} = 2.3 V	-	-	0.36	V
		I _O = 3.1 mA; V _{CC} = 2.3 V	-	-	0.50	V
		I _O = 2.7 mA; V _{CC} = 3.0 V	-	-	0.36	V
		I _O = 4.0 mA; V _{CC} = 3.0 V	-	-	0.50	V

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
l _l	input leakage current	V_{I} = GND to 3.6 V; V_{CC} = 0 V to 3.6 V	-	-	±0.75	μΑ
I _{OZ}	OFF-state output current	$V_I = V_{IH} \text{ or } V_{IL}; V_O = 0 \text{ V to } 3.6 \text{ V};$ $V_{CC} = 0 \text{ V to } 3.6 \text{ V}$	-	-	±0.75	μΑ
I _{OFF}	power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V	-	-	±0.75	μΑ
ΔI_{OFF}	additional power-off leakage current	V_1 or $V_0 = 0$ V to 3.6 V; $V_{CC} = 0$ V to 0.2 V	-	-	±0.75	μΑ
I _{CC}	supply current	$V_I = GND \text{ or } V_{CC}; I_O = 0 \text{ A};$ $V_{CC} = 0.8 \text{ V to } 3.6 \text{ V}$	-	-	1.4	μΑ
ΔI _{CC}	additional supply current	$V_1 = V_{CC} - 0.6 \text{ V}; I_O = 0 \text{ A}; V_{CC} = 3.3 \text{ V}$	-	-	75	μΑ

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Fig. 8.

Symbol	Parameter	Conditions			25 °C		-40	°C to +12	25 °C	Unit
				Min	Typ [1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 5 p	F									
t _{pd}	propagation	nA, nB to nY; see Fig. 7	[2]							
	delay	V _{CC} = 0.8 V		-	13.5	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		1.9	4.6	10.4	1.8	11.4	12.6	ns
		V _{CC} = 1.4 V to 1.6 V		1.5	3.3	6.5	1.4	7.4	8.2	ns
		V _{CC} = 1.65 V to 1.95 V		1.2	2.9	5.1	1.1	5.9	6.5	ns
		V _{CC} = 2.3 V to 2.7 V		1.0	2.2	3.8	0.9	4.5	4.9	ns
		V _{CC} = 3.0 V to 3.6 V		0.9	2.3	4.0	0.8	4.5	4.9	ns
C _L = 10	pF							_		
t _{pd}	propagation	nA, nB to nY; see Fig. 7	[2]							
	delay	V _{CC} = 0.8 V		-	16.3	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		2.3	5.6	12.3	2.1	13.7	15.1	ns
		V _{CC} = 1.4 V to 1.6 V		1.8	4.1	7.6	1.7	8.8	9.7	ns
		V _{CC} = 1.65 V to 1.95 V		1.6	3.8	6.1	1.4	7.1	7.8	ns
		V _{CC} = 2.3 V to 2.7 V		1.4	2.9	4.6	1.2	5.4	5.9	ns
		V _{CC} = 3.0 V to 3.6 V		1.3	3.2	5.7	1.1	6.4	7.0	ns
C _L = 15	pF							1	<u> </u>	
t _{pd}	propagation	nA, nB to nY; see Fig. 7	[2]							
	delay	V _{CC} = 0.8 V		-	19.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V		2.6	6.6	14.2	2.4	15.8	17.4	ns
		V _{CC} = 1.4 V to 1.6 V		2.1	4.8	8.7	1.9	10.1	11.1	ns
		V _{CC} = 1.65 V to 1.95 V		1.9	4.6	7.6	1.7	8.5	9.3	ns
		V _{CC} = 2.3 V to 2.7 V		1.6	3.6	5.6	1.5	6.3	6.9	ns
		V _{CC} = 3.0 V to 3.6 V		1.6	4.1	7.5	1.4	8.3	9.1	ns

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Symbol	Parameter	Conditions		25 °C		-40 °C to +125 °C			Unit
			Min	Typ [1]	Max	Min	Max (85 °C)	Max (125 °C)	
C _L = 30	pF								
t _{pd}	propagation	nA, nB to nY; see Fig. 7 [2							
	delay	V _{CC} = 0.8 V	-	27.0	-	-	-	-	ns
		V _{CC} = 1.1 V to 1.3 V	3.6	9.5	19.5	3.2	21.8	24.0	ns
		V _{CC} = 1.4 V to 1.6 V	2.9	7.0	11.5	2.6	13.6	15.0	ns
		V _{CC} = 1.65 V to 1.95 V	2.6	7.0	12.1	2.3	13.3	14.6	ns
		V _{CC} = 2.3 V to 2.7 V	2.4	5.4	8.9	2.1	9.9	10.9	ns
		V _{CC} = 3.0 V to 3.6 V	2.3	6.5	12.7	2.1	13.9	15.3	ns
C _L = 5 p	F, 10 pF, 15 pF	and 30 pF	<u>'</u>						
C _{PD}	power	$f = 1 \text{ MHz}; V_I = \text{GND to } V_{CC}$ [3							
	dissipation capacitance	V _{CC} = 0.8 V	-	0.6	-	-	-	-	pF
	Capacitance	V _{CC} = 1.1 V to 1.3 V	-	0.7	-	-	-	-	pF
		V _{CC} = 1.4 V to 1.6 V	-	0.8	-	-	-	-	pF
		V _{CC} = 1.65 V to 1.95 V	-	0.9	-	-	-	-	pF
		V _{CC} = 2.3 V to 2.7 V	-	1.1	-	-	-	-	pF
		V _{CC} = 3.0 V to 3.6 V	-	1.4	-	-	-	-	pF

 f_i = input frequency in MHz;

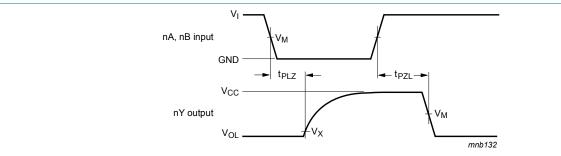
V_{CC} = supply voltage in V;

N = number of inputs switching.

 ^[1] All typical values are measured at nominal V_{CC}.
 [2] t_{pd} is the same as t_{PZL} and t_{PLZ}.
 [3] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).
 P_D = C_{PD} × V_{CC}² × f_i × N where:

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11.1. Waveforms and test circuit



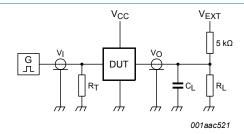
Measurement points are given in <u>Table 9</u>.

 V_{OL} is a typical output voltage level that occurs with the output load.

Fig. 7. The data input (nA, nB) to output (nY) propagation delays

Table 9. Measurement points

Supply voltage	Input	Output				
V _{CC}	V _M	V _M	V _X			
0.8 V to 1.6 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.1 V			
1.65 V to 2.7 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.15 V			
3.0 V to 3.6 V	0.5V _{CC}	0.5V _{CC}	V _{OL} + 0.3 V			



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

 R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

Fig. 8. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V _{EXT}		
V _{CC}	CL	R _L [1]	t _{PLH} , t _{PHL}	t _{PZH} , t _{PHZ}	t _{PZL} , t _{PLZ}
0.8 V to 3.6 V	5 pF, 10 pF, 15 pF and 30 pF	5 kΩ or 1 MΩ	open	GND	2V _{CC}

[1] For measuring enable and disable times R_L = 5 k Ω .

For measuring propagation delays, set-up times, hold times and pulse width, R_L = 1 $M\Omega$.

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12. Package outline

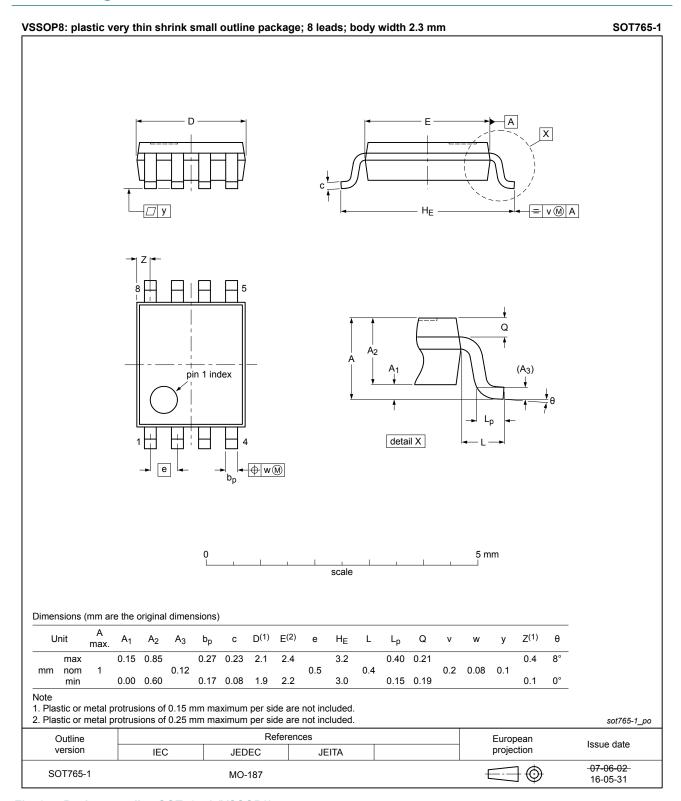


Fig. 9. Package outline SOT765-1 (VSSOP8)

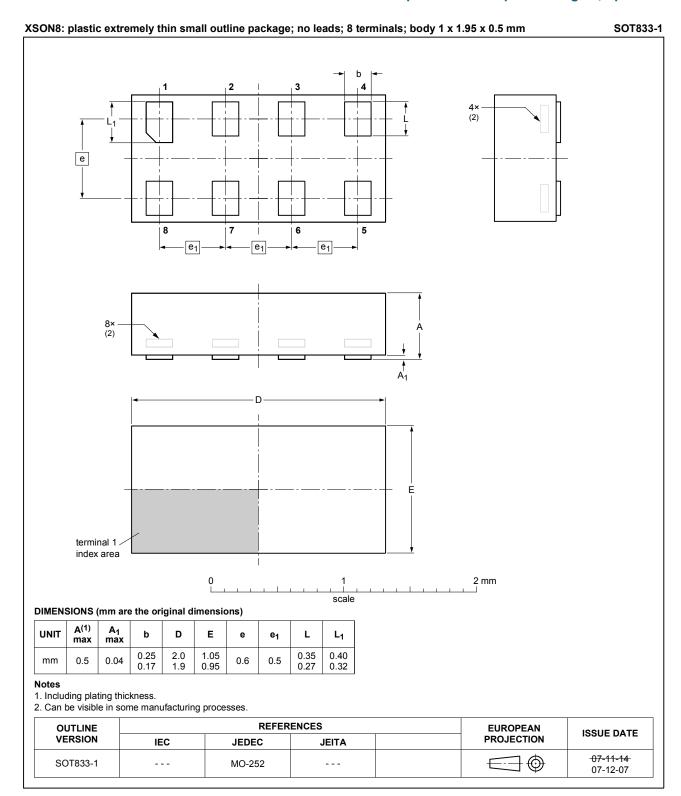


Fig. 10. Package outline SOT833-1 (XSON8)

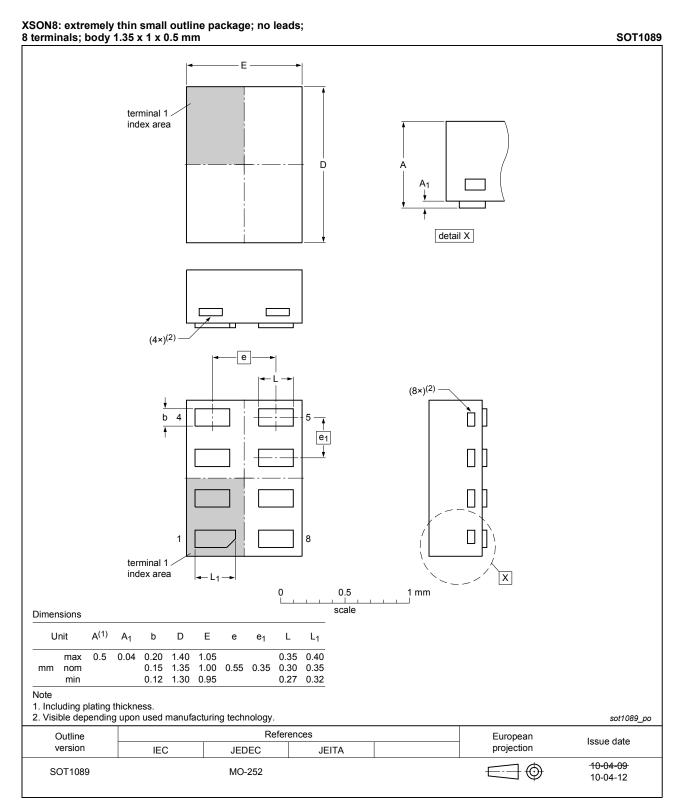


Fig. 11. Package outline SOT1089 (XSON8)

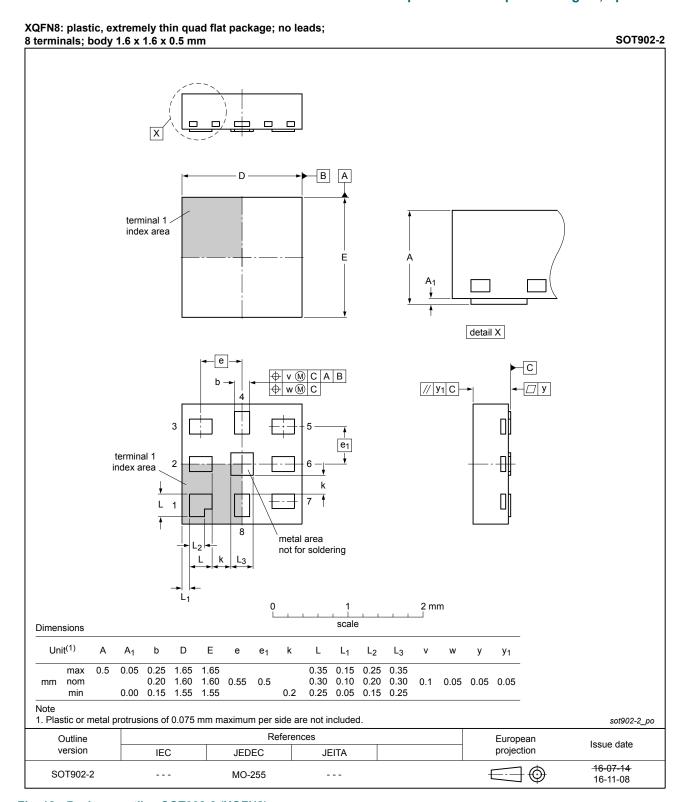


Fig. 12. Package outline SOT902-2 (XQFN8)

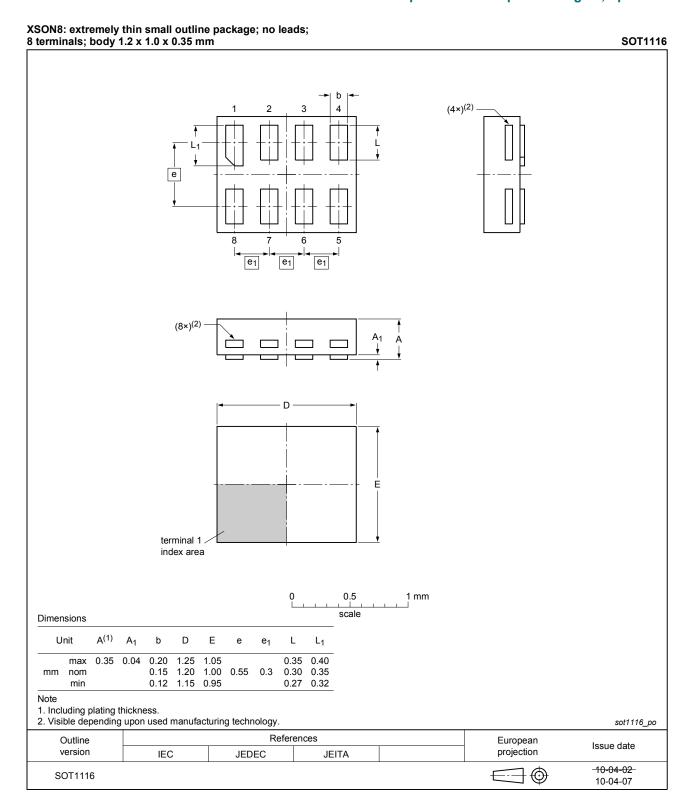


Fig. 13. Package outline SOT1116 (XSON8)

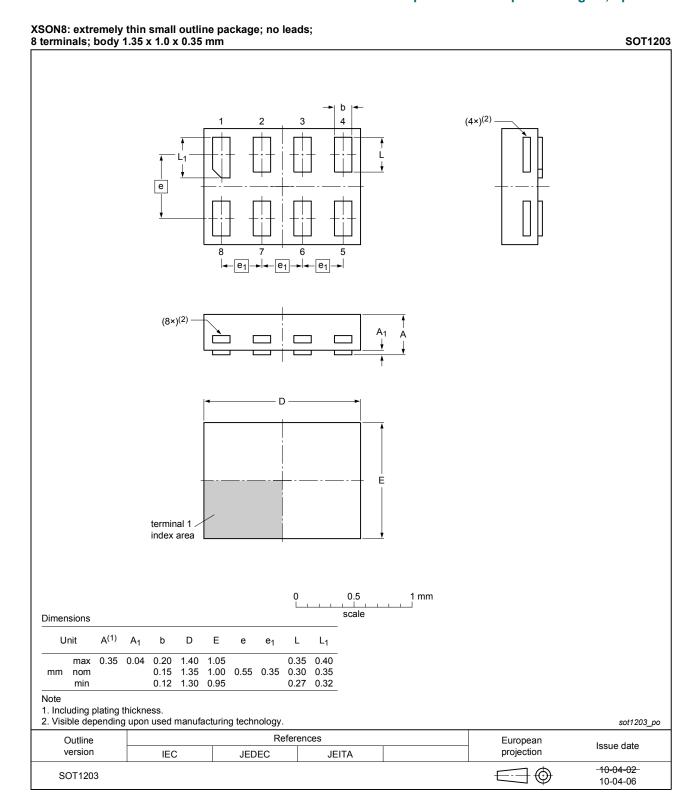


Fig. 14. Package outline SOT1203 (XSON8)

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13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
DUT	Device Under Test
ESD	ElectroStatic Discharge
НВМ	Human Body Model
MM	Machine Model

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
74AUP2G38 v.9	20190326	Product data sheet	-	74AUP2G38 v.8		
Modifications:	of Nexperia • Legal texts	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Type numbers 74AUP2G38GD (SOT996-2) removed. 				
	Package of	utline drawing SOT902-2 utline drawing SOT902-2	(VSSOP8) updated.			
74AUP2G38 v.8	20130211	Product data sheet	-	74AUP2G38 v.7		
Modifications:	For type nu	For type number 74AUP2G38GD XSON8U has changed to XSON8.				
74AUP2G38 v.7	20120605	Product data sheet	-	74AUP2G38 v.6		
74AUP2G38 v.6	20111209	Product data sheet	-	74AUP2G38 v.5		
74AUP2G38 v.5	20100923	Product data sheet	-	74AUP2G38 v.4		
74AUP2G38 v.4	20091008	Product data sheet	-	74AUP2G38 v.3		
74AUP2G38 v.3	20090616	Product data sheet	-	74AUP2G38 v.2		
74AUP2G38 v.2	20080312	Product data sheet	-	74AUP2G38 v.1		
74AUP2G38 v.1	20061016	Product data sheet	-	-		

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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